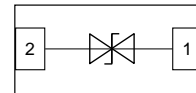
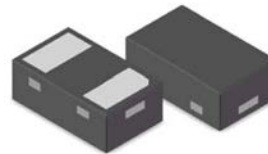




: YUi fYg

- 250Watts peak pulse power ($T_P = 8/20\mu s$)
- DFN1006-2 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Medium capacitance ($C_j = 25\text{pF typ.}$)
- Protection one data/power line to:
 - IEC 61000-4-2 $\pm 30\text{kV}$ contact $\pm 30\text{kV}$ air
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 8A (8/20 μs)



A YW Ub]WU`8 UHU

- 7 UgY. DFN1006-2 $\text{Cj} = 25\text{pF}$ Halogen free
- Ac`X]b[`7 ca dci bX: `Ua a UW]]miFU]b[.
- Hyfa]bUg. $P_{PP} = 250\text{W}$, $T_P = 8/20\mu s$

Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants (PDAs)
- Notebooks & Handhelds
- Portable Instrumentation

5 Vgc`i hY`AU]a i a `FU]b[g

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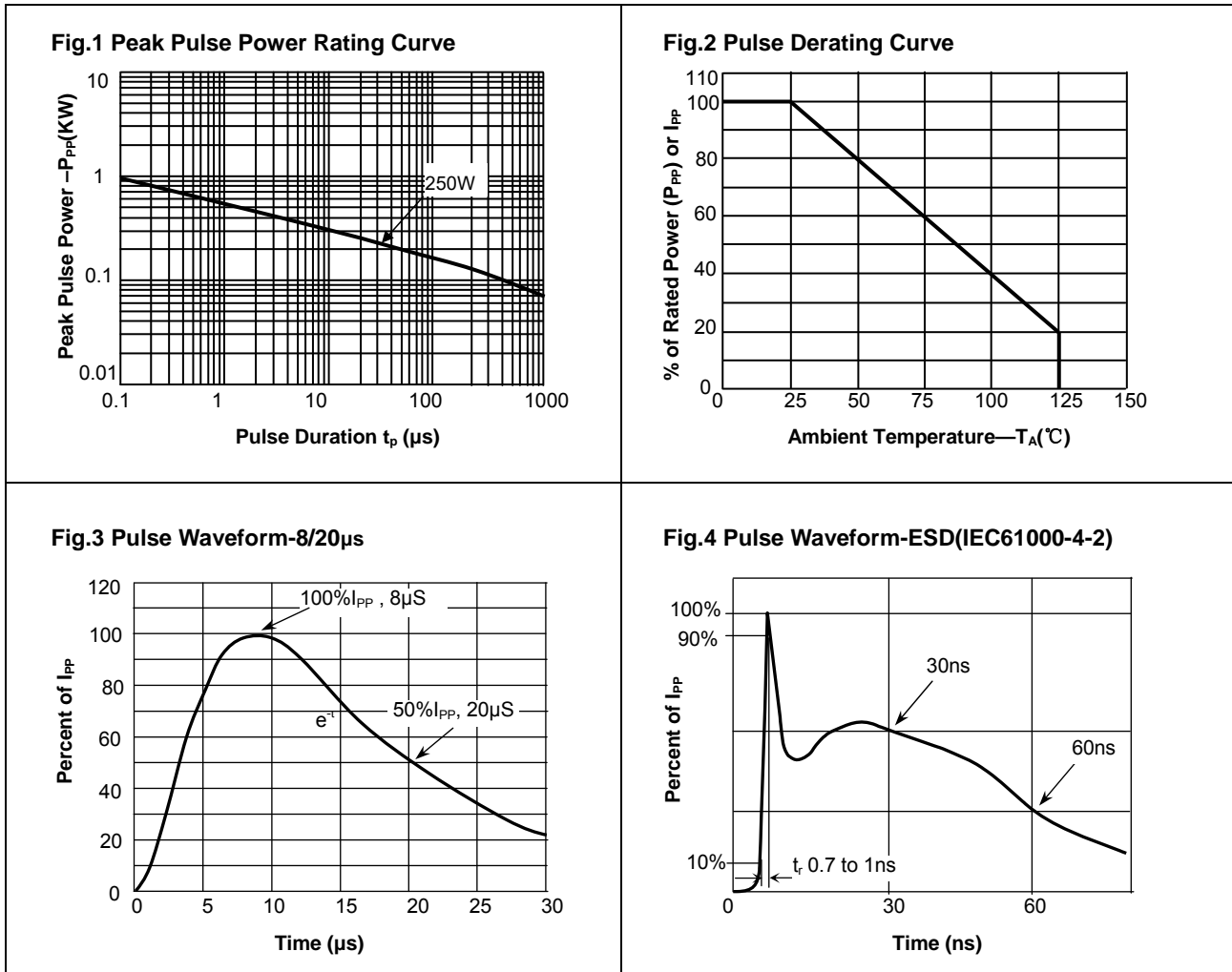
Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_P = 8/20\mu s$)	P_{PP}	250	W
ESD contact/air discharge (IEC-61000-4-2)	V_{ESD}	30/30	kV
Peak Pulse Current ($T_P = 8/20\mu s$)	I_{PP}	8	A
Junction Temperature	T_J	-55 to +125	$^{\circ}\text{C}$
Storage temperature	T_{STG}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics

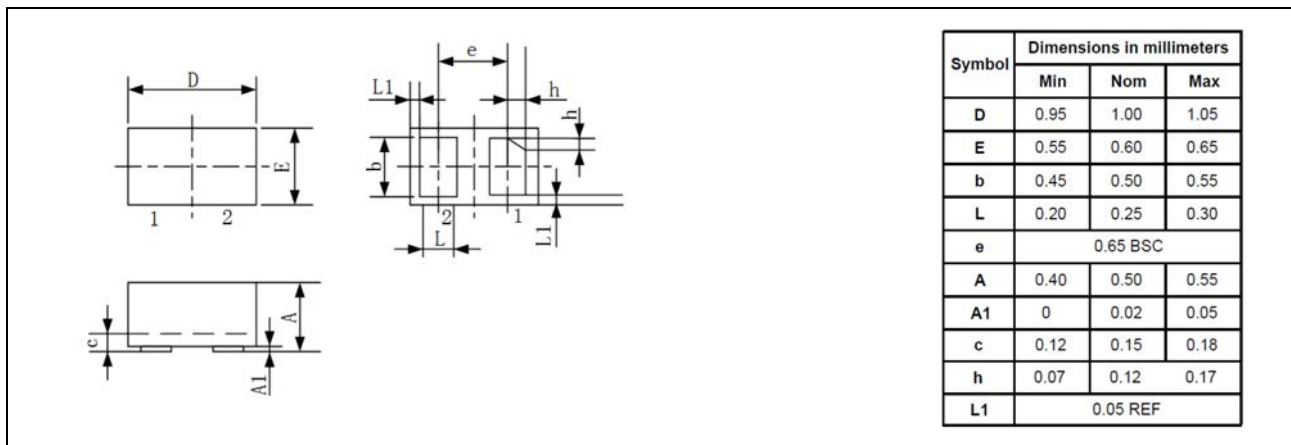
($T_A = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse stand-off Voltage	V_{RWM}				15.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	16.7			V
Reverse Leakage Current	I_R	$V_R = 15\text{V}$			0.5	μA
Clamping Voltage (IEC 61000-4-5)	V_C	$I_{PP} = 8\text{A}$			32	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$		25		pF

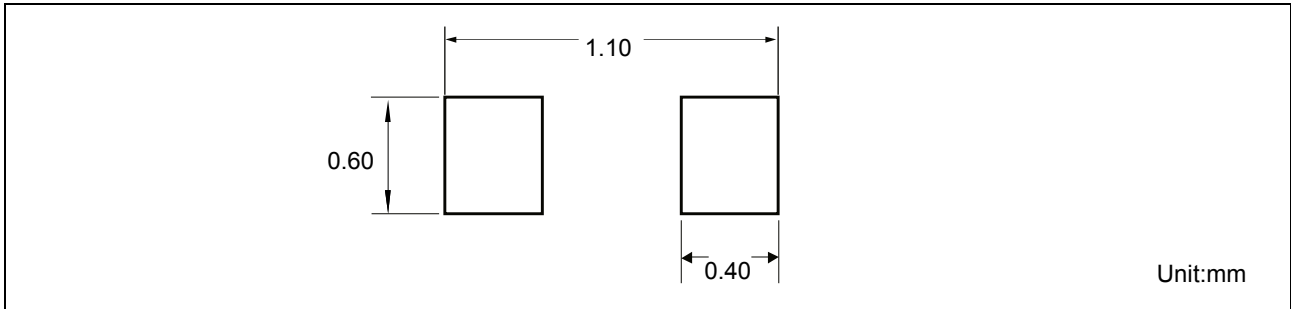
Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)



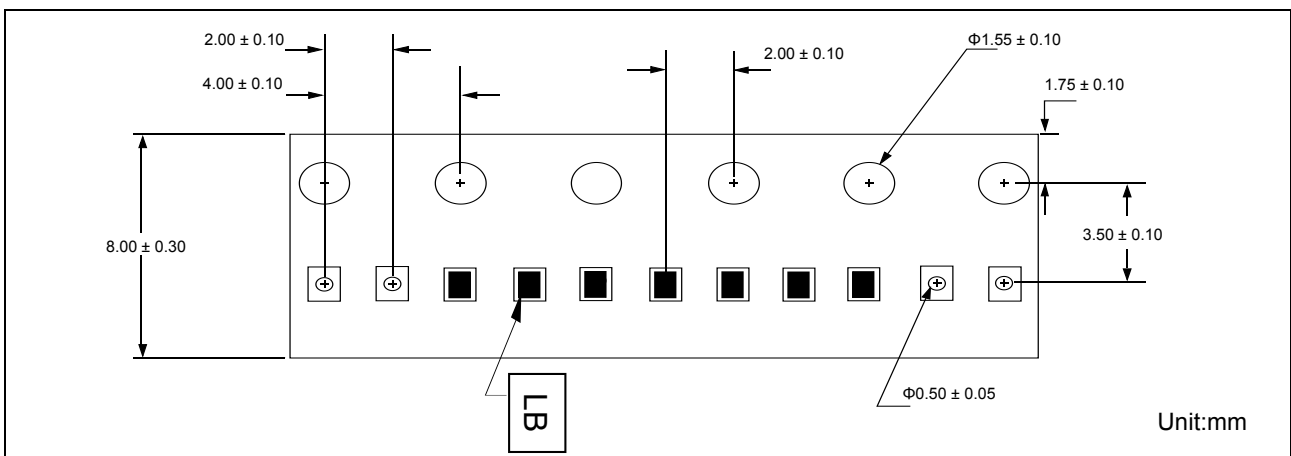
Package Dimensions



Pad Dimensions



Tape and Reel Specification



Marking



Ordering information

Order code	Package	Packaging option	Base quantity	Packaging specification
YEDD1021508AG	DFN1006-2	Tape and reel	10000pcs / reel	EIA STD RS-481